TOSHIBA

• 9097247 0021487 633

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

POWER GaAs MMIC TMD0507-2

Features:

HIGH POWER

■ BROAD BAND INTERNALLY MATCHED

PidB= 33 dBm at 5.1 to 7.2 GHz

HIGH GAIN

HERMETICALLY SEALED PACKAGE

G1dB= 22 dB at 5.1 to 7.2 GHz

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	٧	15
GATE SUPPLY VOLTAGE	Vgg	V	-10
INPUT POWER	Pin	W	0. 1
FLANGE TEMPERATURE	Tf	${\mathfrak C}$	-30~+80
STORAGE TEMPERATURE	Tstg	$^{\circ}$	-65∼+175

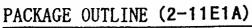
RF CHARACTERISTICS (Ta=25℃)

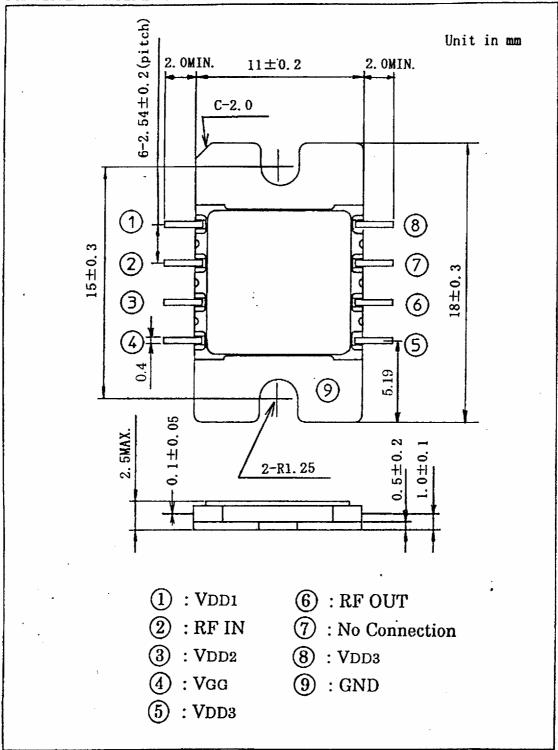
CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB	PidB	VDD1=VDD2=VDD3=	dBm	32. 0	33. 0	_
Gain Compression Point		10V,				
Power Gain at 1 dB	G1dB	VGG=-5 V	dB	20. 0	22. 0	_
Gain Compression Point		f= 5.1-7.2 GHz			•	
Drain Current	IDD *		A		1. 70	2. 00
Input VSWR	VSWRi				1	3. 0

^{*} IDD=IDD1+IDD2+IDD3

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HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torques are 0.18-0.20 N·m.